

Li Wan

List of Publications by Year in descending order

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713013

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42
all docs

42
docs citations

42
times ranked

679
citing authors

#	ARTICLE	IF	CITATIONS
1	Excitations of atomic vibrations in amorphous solids. Journal of Physics Condensed Matter, 2021, 33, 155401.	0.7	0
2	Poissonâ€“Boltzmann equation with a random field for charged fluids. Journal of Physics Condensed Matter, 2019, 31, 375101.	0.7	0
3	Catalyst free N-doped carbon nanotube arrays based on a ZnO nanorod template with high performance field emission. Journal of Materials Chemistry C, 2019, 7, 8730-8736.	2.7	10
4	Impurity-induced environmental quantum phase transitions in the quadratic-coupling spin-boson model. Physical Review B, 2018, 98, .	1.1	3
5	Quantum noise theory for phonon transport through nanostructures. Physica B: Condensed Matter, 2017, 510, 22-28.	1.3	3
6	Controllable Ag nanoparticle coated ZnO nanorod arrays on an alloy substrate with enhanced field emission performance. RSC Advances, 2017, 7, 46760-46766.	1.7	16
7	Slip length of confined liquid with small roughness of solid-liquid interfaces. Physical Review E, 2017, 95, 043107.	0.8	3
8	Enhanced photoluminescence and phosphorescence properties of green phosphor Zn ₂ GeO ₄ :Mn ²⁺ via composition modification with GeO ₂ and MgF ₂ . Dalton Transactions, 2016, 45, 9506-9512.	1.6	15
9	The Poissonâ€“Boltzmann equation and the charge separation phenomenon at the silica-water interface: A holistic approach. Annals of Mathematical Sciences and Applications, 2016, 1, 217-249.	0.2	2
10	Self-Consistent Approach to Global Charge Neutrality in Electrokinetics: A Surface Potential Trap Model. Physical Review X, 2014, 4, .	2.8	14
11	Properties of a Ni-FUSI gate formed by the EBV method and one-step RTA. Journal of Semiconductors, 2012, 33, 036003.	2.0	0
12	Electronic structures in a CdSe spherical quantum dot in a magnetic field: Diagonalization method and variational method. Journal of Applied Physics, 2012, 111, .	1.1	25
13	Analytical solutions to zeroth-order dispersion relations of a cylindrical metallic nanowire near the backbending point. European Physical Journal B, 2012, 85, 1.	0.6	4
14	Studies on H ₂ O-based Atomic Layer Deposition of Al ₂ O ₃ Dielectric on Pristine Graphene. Wujii Cailiao Xuebao/Journal of Inorganic Materials, 2012, 27, 956-960.	0.6	3
15	Thermal dependence of the optical gain and threshold current density of GaInNAs/GaAs/AlGaAs quantum well lasers. Journal of Applied Physics, 2011, 110, 123109.	1.1	5
16	Effects of Laser in situ annealing on crystal quality of NiSi film grown on Si(001) substrate. Thin Solid Films, 2010, 518, 3646-3649.	0.8	5
17	Synthesis, characterization and optical properties of flower-like tellurium. CrystEngComm, 2010, 12, 166-171.	1.3	40
18	Polarized Raman spectroscopy study of NiSi film grown on Si(001) substrate. Applied Physics A: Materials Science and Processing, 2009, 97, 693-697.	1.1	2

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19	Raman active modes of NiSi crystal. <i>Physica B: Condensed Matter</i> , 2009, 404, 2324-2326.	1.3	2
20	Annealing effects on microstructures of HfAlO/Si with a Ti capping layer. <i>EPJ Applied Physics</i> , 2009, 48, 20302.	0.3	1
21	Identification of the Structures of Superlong Oriented Single-Walled Carbon Nanotube Arrays by Electrodeposition of Metal and Raman Spectroscopy. <i>Journal of the American Chemical Society</i> , 2008, 130, 11860-11861.	6.6	35
22	Structure properties of BiFeO ₃ films studied by micro-Raman scattering. <i>Journal of Applied Physics</i> , 2008, 103, .	1.1	118
23	Interfacial structures and electrical properties of HfAl ₂ O ₅ gate dielectric film annealed with a Ti capping layer. <i>Applied Physics Letters</i> , 2007, 90, 152910.	1.5	10
24	Tilt growth of the epilayer with large lattice mismatch to the substrate. <i>EPJ Applied Physics</i> , 2007, 38, 231-238.	0.3	3
25	Tilt growth of MnAs on the GaAs(001) substrate. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2007, 367, 373-378.	0.9	2
26	Observation of antiphase domains in BiFeO ₃ thin films by X-ray diffraction. <i>Physica B: Condensed Matter</i> , 2007, 391, 124-129.	1.3	5
27	Thickness dependence of the magnetic properties of MnAs films on GaAs(001) and GaAs(113)A: Role of a natural array of ferromagnetic stripes. <i>Journal of Applied Physics</i> , 2004, 96, 5056-5062.	1.1	42
28	Lateral periodicity of elastic domains in MnAs/GaAs(001) epitaxial layers studied by high resolution X-ray diffraction. <i>Zeitschrift Fur Kristallographie - Crystalline Materials</i> , 2004, 219, .	0.4	7
29	Title is missing!. <i>Journal of Materials Science Letters</i> , 2003, 22, 1581-1583.	0.5	5
30	Transmission electron microscopy and atomic force microscopy studies of GaN films grown on AlAs/GaAs(001) substrates. <i>Journal of Crystal Growth</i> , 2003, 252, 517-522.	0.7	1
31	Microstructure of GaN films grown on Si(111) substrates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2003, 256, 416-423.	0.7	15
32	Defects in GaN Films Grown on Si(111) Substrates by Metal-Organic Chemical Vapour Deposition. <i>Chinese Physics Letters</i> , 2003, 20, 1811-1814.	1.3	2
33	Effect of rapid thermal annealing on the structural characteristics of cubic GaN epilayer grown on GaAs (001) substrates by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2001, 222, 503-506.	0.7	0
34	Nucleation of hexagonal AlN in nitridized AlAs buffer on (001) GaAs substrate. <i>Journal of Crystal Growth</i> , 2001, 222, 507-510.	0.7	3
35	Epitaxial growth and characterization of GaN Films on (001) GaAs substrates by radio-frequency molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2001, 227-228, 390-394.	0.7	3
36	Photoluminescence study of Si doping cubic GaN grown on (001) GaAs substrates by Molecular Beam Epitaxy. <i>Journal of Crystal Growth</i> , 2001, 227-228, 420-424.	0.7	4

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37	Growth and properties of hexagonal GaN on GaAs(001) substrate by RF-molecular beam epitaxy using an AlAs nucleation layer. Journal of Crystal Growth, 2000, 212, 391-396.	0.7	4
38	MBE growth and Raman studies of cubic and hexagonal GaN films on (001)-oriented GaAs substrates. Journal of Crystal Growth, 2000, 218, 191-196.	0.7	20
39	Transmission electron microscopy study of hexagonal GaN film grown on GaAs (001) substrate by using AlAs nucleation layer. Journal of Crystal Growth, 2000, 220, 379-383.	0.7	5
40	Controllable cubic and hexagonal GaN growth on GaAs(001) substrates by molecular beam epitaxy. Journal of Crystal Growth, 2000, 210, 811-814.	0.7	11
41	Influence of AlN Buffer on Phase Structure of GaN on GaAs (001) Grown by Radio-Frequency Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2000, 39, 4704-4706.	0.8	8
42	Influence of Si doping on optical characteristics of cubic GaN grown on (001) GaAs substrates. Applied Physics Letters, 2000, 76, 3765-3767.	1.5	17